

## N - CHANNEL ENHANCEMENT MODE POWER MOSFET

**TF030N03M**

### • General Description

The TF030N03M uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

### • Features

Advance device construction

Low  $R_{DS(ON)}$  to minimize conduction loss

Low Gate Charge for fast switching

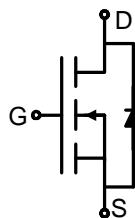
Low Thermal resistance

### • Application

Synchronous Rectification for AC-DC/DC-DC converter

Power Tools

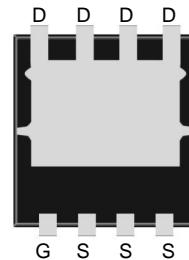
### • Product Summary



$V_{DS} = 30V$   $I_D = 70A$

$R_{DS(on)(10V)} = 3.0m\Omega$

$R_{DS(on)(4.5V)} = 4.8m\Omega$



**PDFNWB3.3x3.3-8L**

### • Package Marking and Ordering Information:

Part NO.	TF030N03M
Marking1	030N03M
Marking2	TF:tuofeng; AA:device code; Y:year code; X:Week
Basic ordering unit (pcs)	5000

### • Absolute Maximum Ratings ( $T_C = 25^\circ C$ )

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	70	A
	$I_D @ T_C = 75^\circ C$	49	A
	$I_D @ T_C = 100^\circ C$	42	A
Pulsed Drain Current ①	$I_{DM}$	210	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	50	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	1.0	W
Operating Junction Temperature	$T_J$	-55 to 150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	$E_{AS}$	100	mJ



Shenzhen Tuofeng Semiconductor Technology Co., Ltd

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### • Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub>	-	-	4.5	° C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	55	° C/W
Soldering temperature, wavesoldering for 8 s	T <sub>sold</sub>	-	-	265	° C

### • Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250uA	30	-	-	V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250uA	1.1	1.5	2.1	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =30 V <sub>GS</sub> = 0V	-	-	1.0	uA
Gate- Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V , V <sub>DS</sub> = 0V	-	-	±100	nA
Static Drain-source On Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	3.0	4.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	4.8	6.0	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 25V, I <sub>D</sub> =20A	-	30	-	S
Source-drain voltage	V <sub>SD</sub>	I <sub>S</sub> =30A	-	-	1.20	V

### • Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C <sub>iss</sub>	f = 1MHz V <sub>DS</sub> =15V V <sub>GS</sub> = 0V	-	2260	-	pF
Output capacitance	C <sub>oss</sub>		-	296	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	230	-	

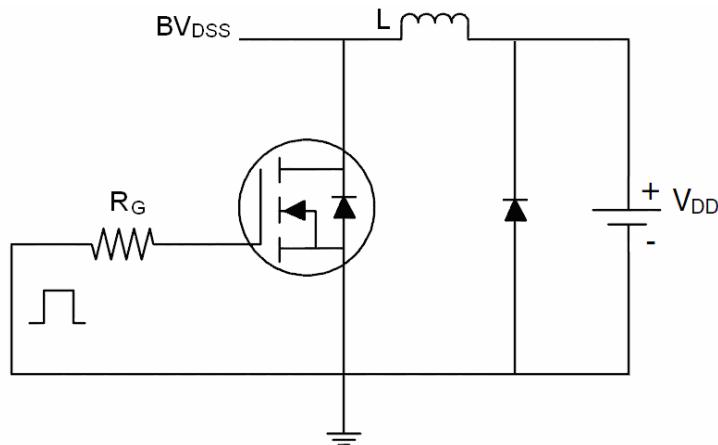
### • Gate Charge characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = 15V I <sub>D</sub> = 15A V <sub>GS</sub> = 10V	-	42	-	nC
Gate - Source charge	Q <sub>gs</sub>		-	9.0	-	
Gate - Drain charge	Q <sub>gd</sub>		-	10	-	

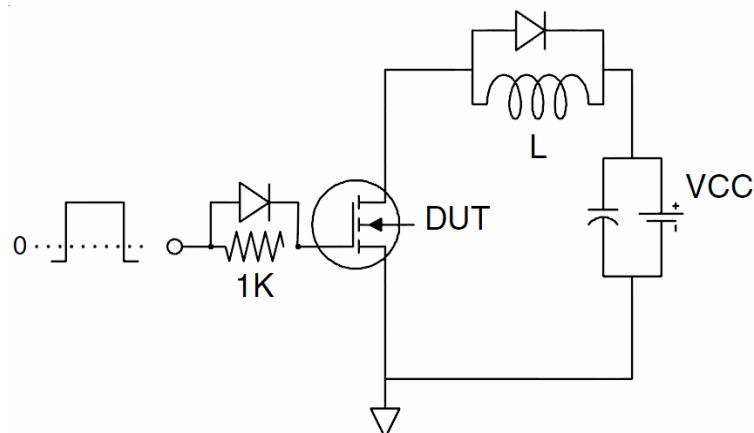
Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

### Test Circuit

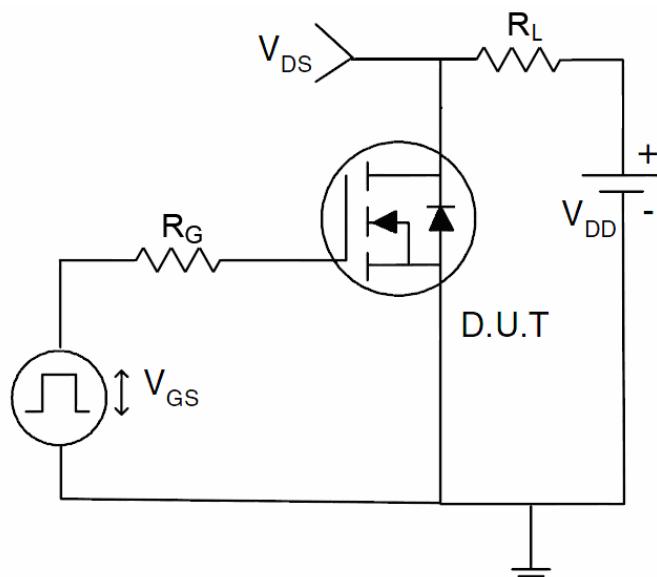
#### 1) E<sub>AS</sub> test Circuit



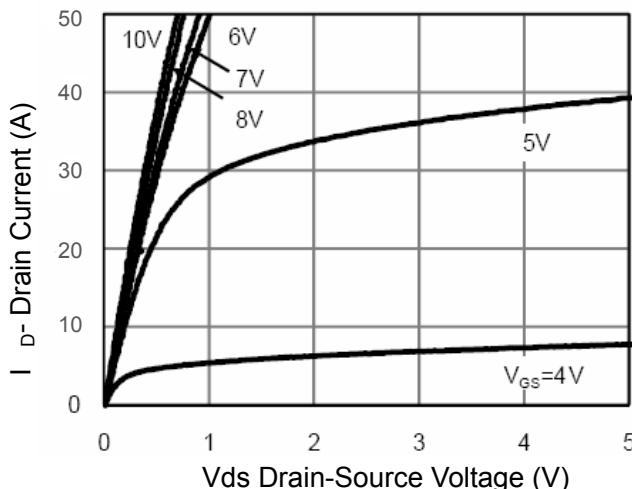
#### 2) Gate charge test Circuit



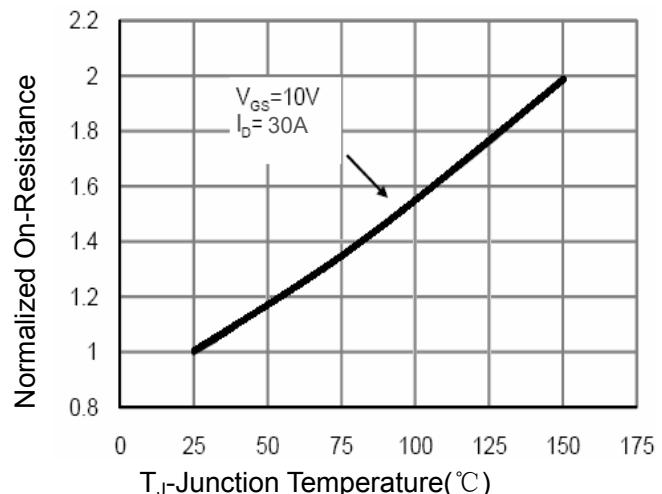
#### 3) Switch Time Test Circuit



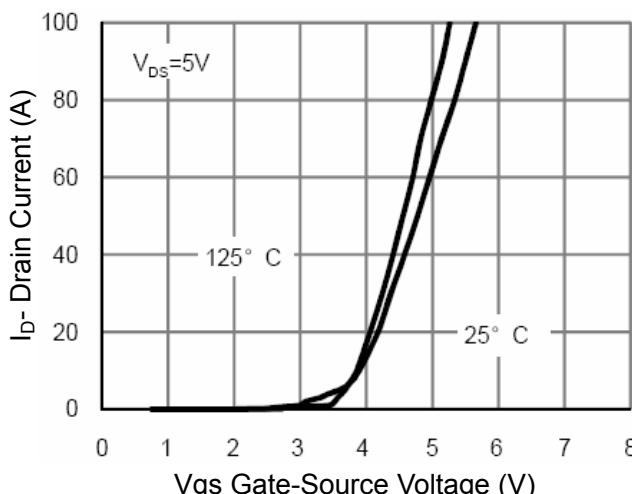
### Typical Electrical and Thermal Characteristics



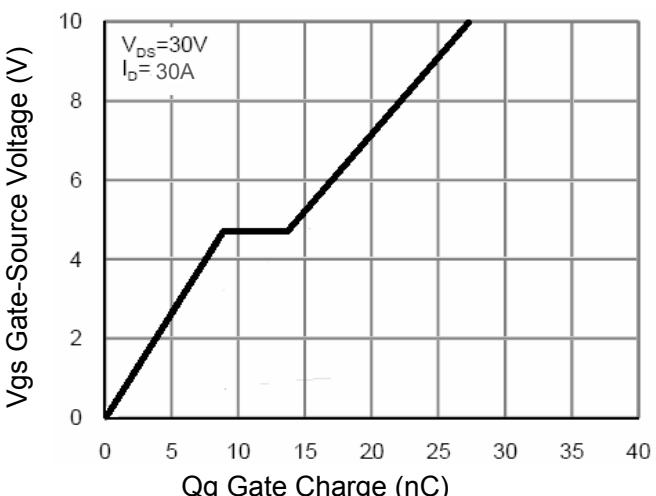
**Figure 1 Output Characteristics**



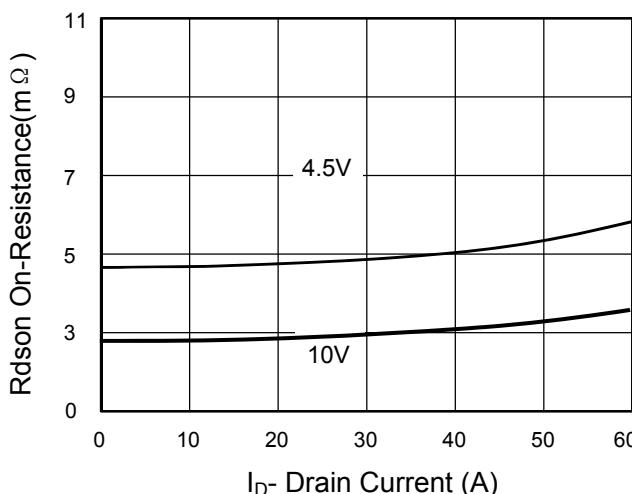
**Figure 4 Rdson-JunctionTemperature**



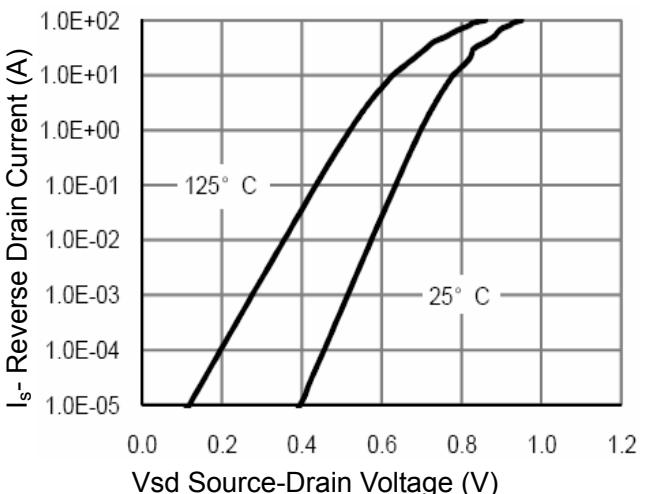
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



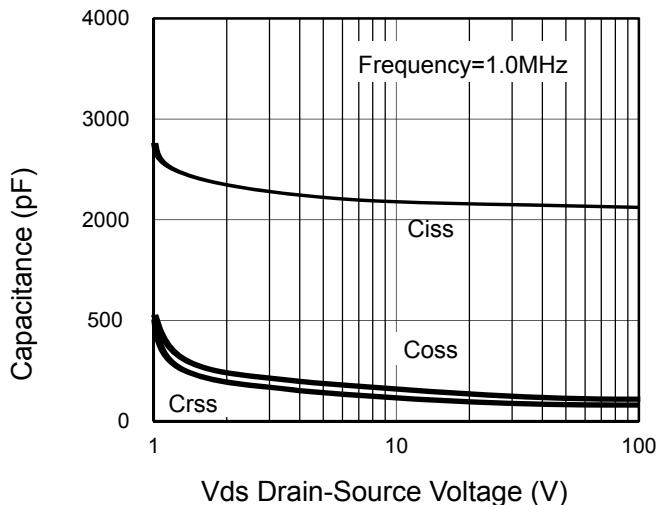
**Figure 3 Rdson- Drain Current**



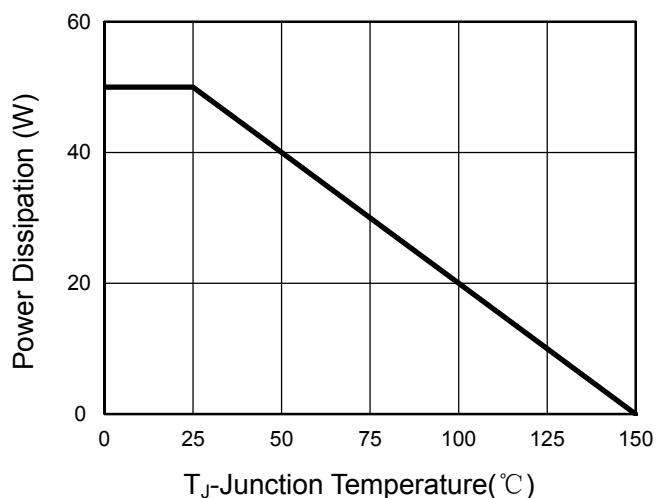
**Figure 6 Source- Drain Diode Forward**

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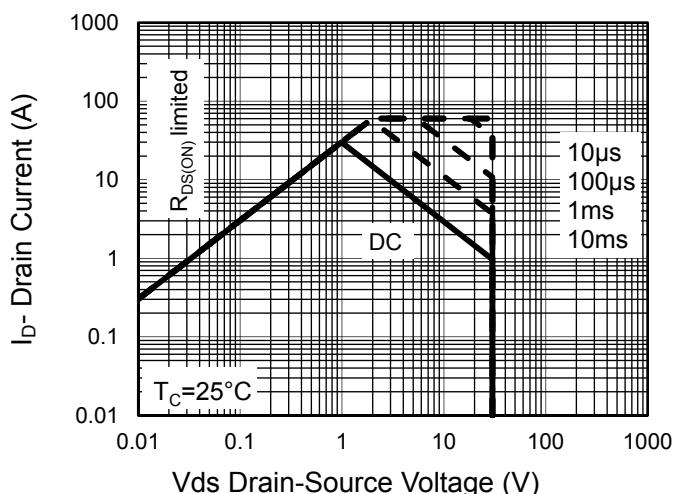
**TF030N03M**



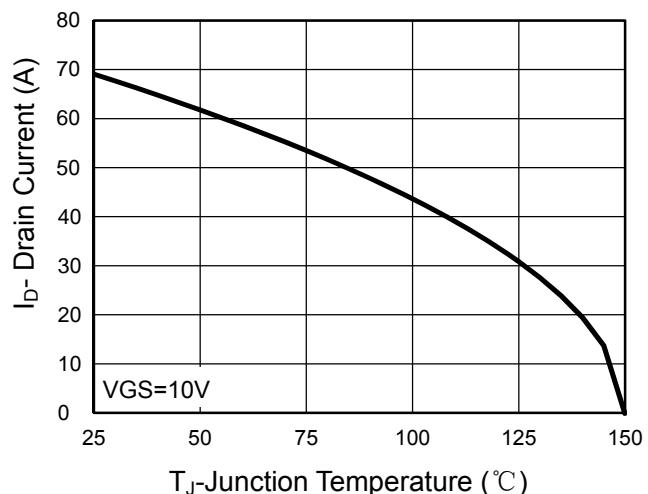
**Figure 7 Capacitance vs Vds**



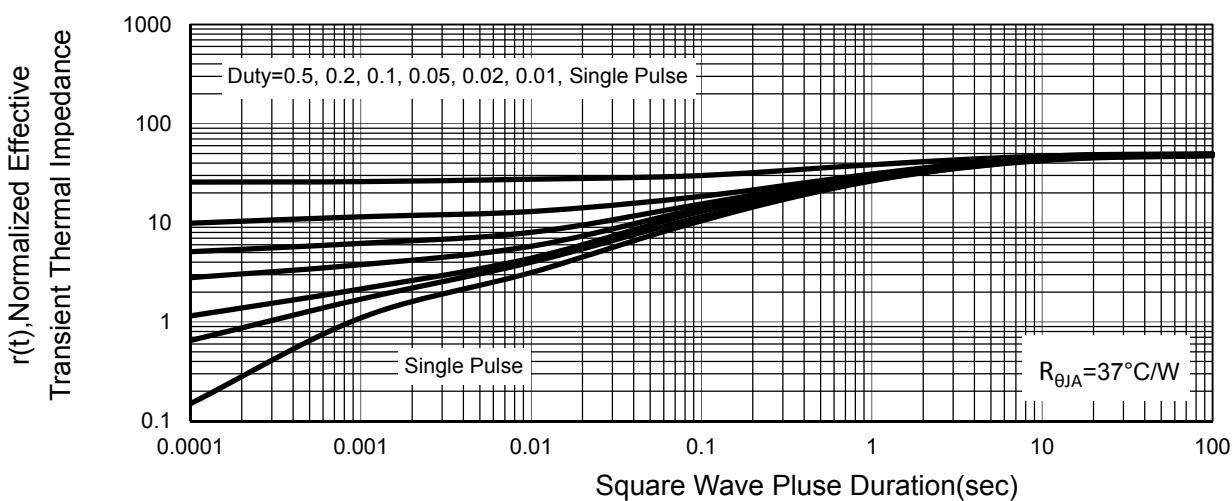
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**



**Figure 10 Current De-rating**

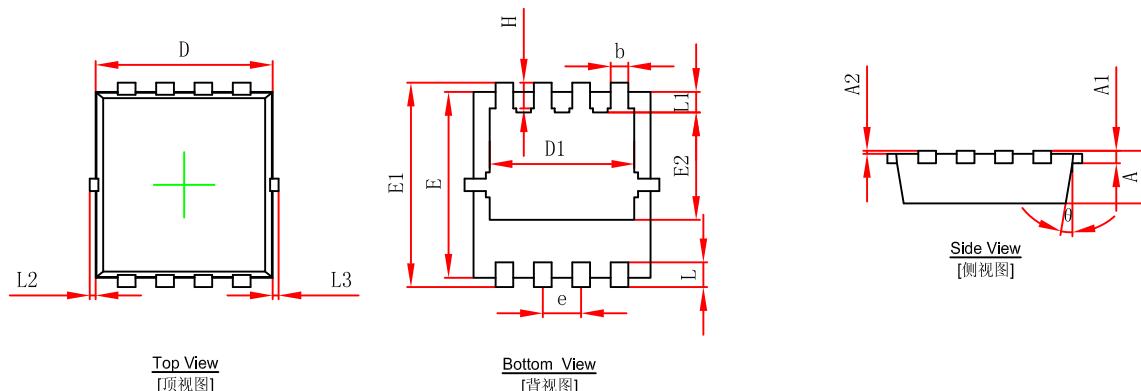


**Figure 11 Normalized Maximum Transient Thermal Impedance**

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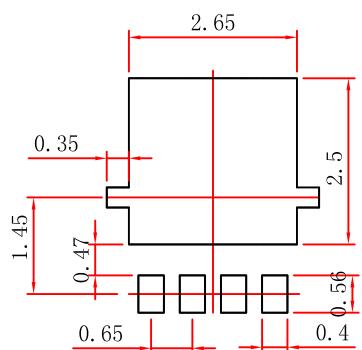
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**PDFNWB3.3x3.3-8L Package Outline Dimensions**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°

**PDFNWB3.3x3.3-8L Suggested Pad Layout**



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$ mm.
3. The pad layout is for reference purposes only.